

MOC223-M

DESCRIPTION

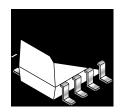
The MOC223-M consists of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon photodarlington detector, in a surface mountable, small outline, plastic package. It is ideally suited for high density applications, and eliminates the need for through - the - board mounting.

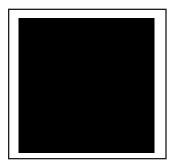
FEATURES

- U.L. Recognized (File #E90700, Volume 2)
- VDE Recognized (File #136616) (add option "V" for VDE approval, i.e, MOC223V-M)
- Industry Standard SOIC-8 Surface Mountable Package with 0.050" lead spacing
- High Current Transfer Ratio of 500% Minimum at I_F = 1 mA
- Standard SOIC-8 Footprint, with 0.050" Lead Spacing
- Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- \bullet High Input-Output Isolation Voltage of 2500 $V_{AC(rms)}$ Guaranteed

APPLICATIONS

- Low Power Logic Circuits
- · Interfacing and coupling systems of different potentials and impedances
- Telecommunications equipment
- · Portable electronics
- · Solid state relays





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C Unless otherwise specified)				
Rating	Symbol	Value	Unit	
EMITTER				
Forward Current - Continuous	I _F	60	mA	
Forward Current - Peak (PW = 100 µs, 120 pps)	I _F (pk)	1.0	Α	
Reverse Voltage	V _R	6.0	V	
LED Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	90 0.8	mW mW/°C	
DETECTOR				
Collector-Emitter Voltage	V _{CEO}	30	V	
Emitter-Collector Voltage	V _{ECO}	7.0	V	
Collector-Base Voltage	V _{CBO}	70	V	
Collector Current-Continuous	I _C	150	mA	
Detector Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	150 1.76	mW mW/°C	
TOTAL DEVICE				
Input-Output Isolation Voltage (f = 60 Hz, t = 1 min.)	V _{ISO}	2500	Vac(rms)	
Total Device Power Dissipation @ T _A = 25°C Derate above 25°C	P_{D}	250 2.94	mW mW/°C	
Ambient Operating Temperature Range	T _A	-40 to +100	°C	
Storage Temperature Range	T _{stg}	-40 to +150	°C	



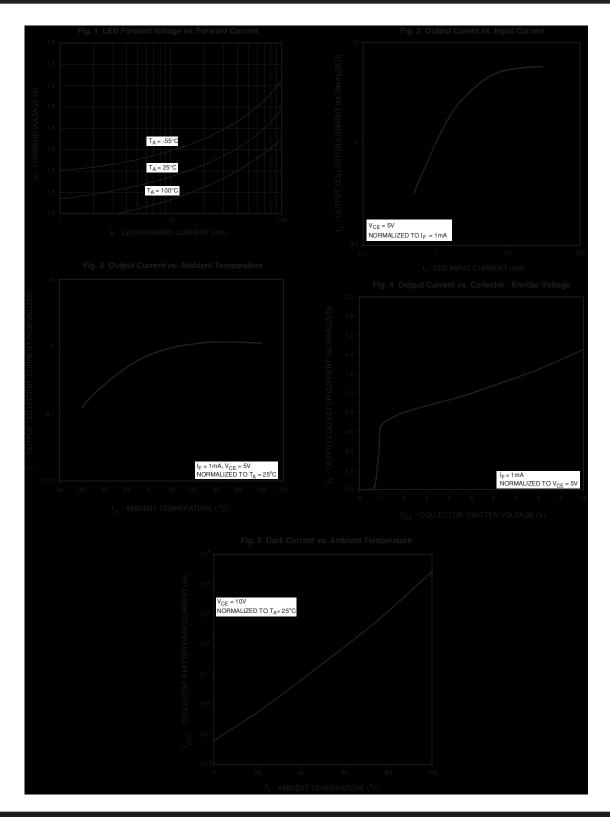
ELECTRICAL CHARACTERISTICS (T _A = 25°C unless otherwise specified)						
Parameter	Test Conditions	Symbol	Min	Тур*	Max	Unit
EMITTER						
Input Forward Voltage	$(I_F = 1.0 \text{ mA})$	V _F	_	1.08	1.3	V
Reverse Leakage Current	$(V_{R} = 6.0 \text{ V})$	I _R	_	0.001	100	μA
Input Capacitance		C _{IN}	_	18	_	pF
DETECTOR						
Collector Emitter Dark Current	$(V_{CE} = 5.0 \text{ V}, T_A = 25^{\circ}\text{C})$	I _{CEO1}	_	1.0	50	nA
Collector-Emitter Dark Current	(V _{CE} = 5.0 V, T _A = 100°C)	I _{CEO2}	_	10	_	μA
Collector-Emitter Breakdown Voltage	(I _C = 100 μA)	BV _{CEO}	30	100	_	V
Emitter-Collector Breakdown Voltage	(I _E = 100 μA)	BV _{ECO}	7.0	10	_	V
Collector-Emitter Capacitance	$(f = 1.0 \text{ MHz}, V_{CE} = 0)$	C _{CE}	_	5.5	_	pF
COUPLED						
Current Transfer Ratio ⁽³⁾	$(I_F = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	CTR	500	1000	_	%
Isolation Surge Voltage ^(1,2)	(f = 60 Hz AC Peak, t = 1 min.)	V _{ISO}	2500	_	_	Vac(rms)
Isolation Resistance ⁽²⁾	(V = 500 V)	R _{ISO}	10 ¹¹	_	_	Ω
Collector-Emitter Saturation Voltage	$(I_C = 500 \mu A, I_F = 1.0 mA)$	V _{CE (sat)}	_	_	1.0	V
Isolation Capacitance ⁽²⁾	$(V_{I-O} = 0 V, f = 1 MHz)$	C _{ISO}	_	0.2	_	pF
Turn-On Time	(fig. 6)(I_F = 5.0 mA, V_{CC} = 10 V, R_L = 100 Ω)	t _{on}	_	3.5	_	μs
Turn-Off Time	(fig. 6)(I_F = 5.0 mA, V_{CC} = 10 V, R_L = 100 Ω)	t _{off}	_	95	_	μs
Rise Time	(fig. 6)(I _F = 5.0 mA, V_{CC} = 10 V, R_L = 100 Ω)	t _r	_	1.0	_	μs
Fall Time	(fig. 6)($I_F = 5.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega$)	t _f	_	2.0	_	μs

^{*}All typicals at $T_A = 25^{\circ}C$

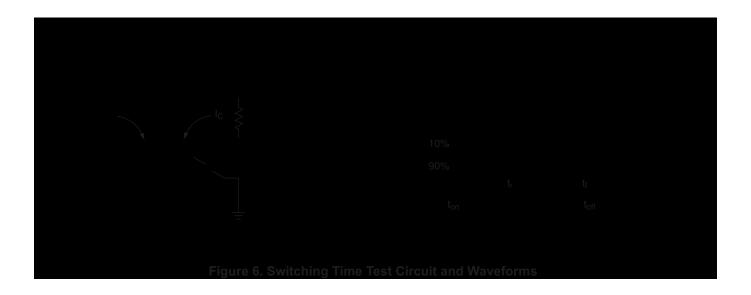
^{1.} Isolation Surge Voltage, $V_{\mbox{\scriptsize ISO}}$, is an internal device dielectric breakdown rating.

^{2.} For this test, Pins 1 and 2 are common and Pins 5, 6 and 7 are common.

^{3.} Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.



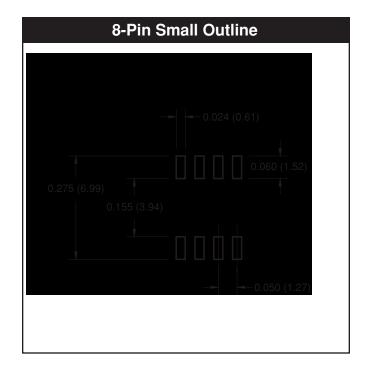






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Package Dimensions (Surface Mount) 0.164 (4.16) 0.144 (3.66) 0.143 (3.63) 0.123 (3.13) 0.021 (0.53) 0.001 (0.28) 0.005 (1.27) Typ Lead Coplanarity: 0.004 (0.10) MAX



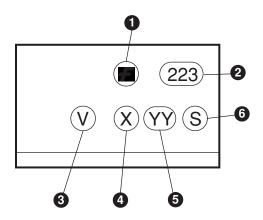


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ORDERING INFORMATION

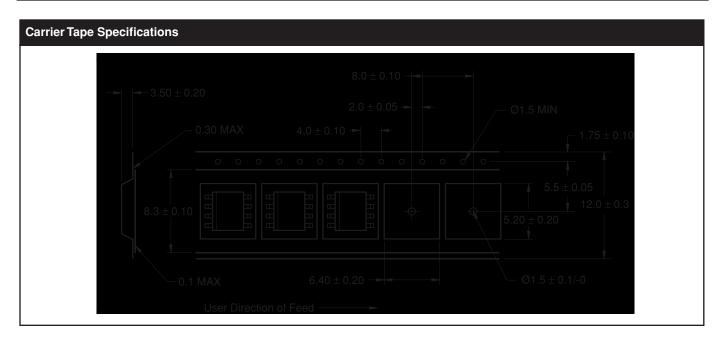
Option	Order Entry Identifier	Description
V	V	VDE 0884
R1	R1	Tape and reel (500 units per reel)
R1V	R1V	VDE 0884, Tape and reel (500 units per reel)
R2	R2	Tape and reel (2500 units per reel)
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)

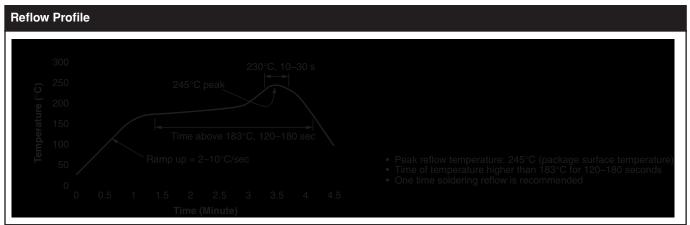
MARKING INFORMATION



Definitions		
1	Fairchild logo	
2	Device number	
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)	
4	One digit year code, e.g., '3'	
5	Two digit work week ranging from '01' to '53'	
6	Assembly package code	

^{*}Note – 'V' option parts marked with date code '325' or earlier are marked in portrait format.







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